	Type	L #	Hits	Search Text	DBs	Time Stamp
1	BRS	L41	846145	mask$6 or photoresist or resist or photo-resist	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/31 11:31
2	BRS	L42	101992	epi or epitaxial	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/31 11:31
3	BRS	L43	883128	gate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/31 11:31
4	BRS	L45	1404205	channel	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/31 11:31
5	BRS	L46	1320994	"gate dielectric" or oxide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/31 11:32

	Type	L #	Hits	Search Text	DBs	Time Stamp
6	BRS	L47	9489	41 and 42 and 43 and 45 and 46	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/31 11:32
7	BRS	L48	2774	47 and fet	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/31 11:33
8	BRS	L49	2751	48 and substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/31 11:33
9	BRS	L50	14941	41 same 42	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/31 11:33
10	BRS	L51	3088	50 same 43	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/31 11:33

	Type	L #	Hits	Search Text	DBs	Time Stamp
11	BRS	L52	1056	51 same 45	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/31 11:34
12	BRS	L53	617	52 and ("field effect transistor" or fet)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/31 11:34
13	BRS	L54	452	53 and (@ad<20001018)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/31 11:39
14	BRS	L55	5025	42 near8 41	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/31 11:39
15	BRS	L56	483	55 same 45	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/31 11:40

	Type	L #	Hits	Search Text	DBs	Time Stamp
16	BRS	L57	90	56 same 43 same 46	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/31 11:41
17	BRS	L58	71	57 and (@ad<20001018)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/31 11:47
18	BRS	L59	2034	channel near4 epitaxial	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/31 11:48
19	BRS	L60	18	remov$6 near4 59	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/31 11:48

	Type	L #	Hits	Search Text	DBs	Time Stamp
1	BRS	L1	819	(((((remov$6 or lift-off) near4 silicon) same channel) and ("field effect transistor" or FET)) and gate) and (@ad<20001018)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/01 14:56
2	BRS	L2	5873	photoresist near4 gate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/01 14:57
3	BRS	L3	199	2 near8 channel	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/01 14:57
4	BRS	L4	157	3 and (@ad<20001018)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/01 14:58
5	BRS	L5	81	4 and ("field effect transistor" or fet)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/01 15:15

	Type	L #	Hits	Search Text	DBs	Time Stamp
6	BRS	L6	5210	double near2 gate$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/01 15:15
7	BRS	L7	168804	"field effect transistor" or fet	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/01 15:15
8	BRS	L8	1268	6 and 7	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/01 15:15
9	BRS	L9	1011	8 and channel	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/01 15:16
10	BRS	L10	588	9 and (@ad<20001018)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/01 15:16

	Type	L #	Hits	Search Text	DBs	Time Stamp
11	BRS	L21	78739	pillar	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/09/01 16:20
12	BRS	L22	624	21 and SOI	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/09/01 16:21
13	BRS	L23	354	22 and ((@ad<20001018) or (@rlad<20001018))	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/09/01 16:22